

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C (Note 8)
60V	3.1mΩ @ V _{GS} = 10V	100A
	4.5mΩ @ V _{GS} = 4.5V	100A

Description and Applications

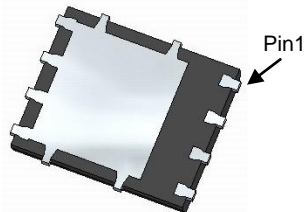
This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Primary Switch in Isolated DC-DC
- Synchronous Rectifier
- Load Switch

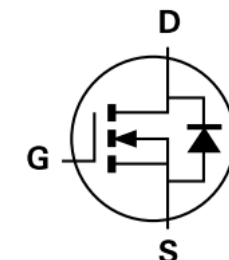
POWERDI®5060-8



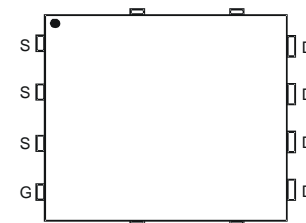
Top View



Bottom View



Internal Schematic


 Top View
Pin Configuration

Mechanical Data

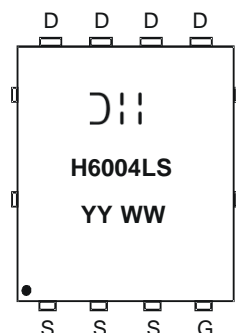
- Case: POWERDI®5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (63)
- Weight: 0.097 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH6004LPS-13	POWERDI®5060-8	2,500 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



☺|| = Manufacturer's Marking
 H6004LS = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Year (ex: 14 = 2014)
 WW = Week (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	60	V
Gate-Source Voltage	V _{GSS}	±20	V
Continuous Drain Current (Note 5)	I _D	T _A = +25°C	22
		T _A = +70°C	16
Continuous Drain Current (Note 6)	I _D	T _C = +25°C	100
		T _C = +100°C (Note 8)	100
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	100	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I _{DM}	120	A
Avalanche Current, L = 0.2mH	I _{AS}	40	A
Avalanche Energy, L = 0.2mH	E _{AS}	160	mJ

Thermal Characteristic

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	T _A = +25°C	2.6
Thermal Resistance, Junction to Ambient (Note 5)		R _{θJA}	47
Total Power Dissipation (Note 6)	P _D	T _C = +25°C	138
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	0.9
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	60	-	-	V	V _{GS} = 0V, I _D = 1mA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μA	V _{DS} = 48V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	-	2.5	3.1	mΩ	V _{GS} = 10V, I _D = 25A
		-	3.3	4.5	mΩ	V _{GS} = 4.5V, I _D = 20A
Diode Forward Voltage	V _{SD}	-	-	1.3	V	V _{GS} = 0V, I _S = 25A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{ISS}	-	4515	-	pF	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz
Output Capacitance	C _{OSS}	-	1477	-		
Reverse Transfer Capacitance	C _{RSS}	-	135.3	-		
Gate Resistance	R _g	-	0.64	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	-	96.3	-	nC	V _{DD} = 30V, I _D = 25A
Total Gate Charge (V _{GS} = 4.5V)	Q _g	-	47.4	-		
Gate-Source Charge	Q _{gs}	-	14.1	-		
Gate-Drain Charge	Q _{gd}	-	21.4	-		
Turn-On Delay Time	t _{D(ON)}	-	9.9	-	ns	V _{DD} = 30V, V _{GS} = 10V, I _D = 25A, R _G = 3.5Ω
Turn-On Rise Time	t _R	-	17.7	-		
Turn-Off Delay Time	t _{D(OFF)}	-	53.5	-		
Turn-Off Fall Time	t _F	-	32.9	-		
Body Diode Reverse Recovery Time	t _{RR}	-	49.7	-	ns	I _F = 25A, di/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	-	78.9	-	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

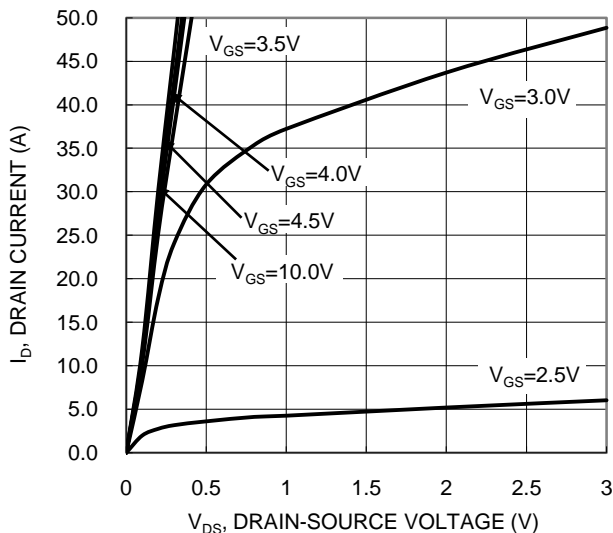


Figure 1. Typical Output Characteristic

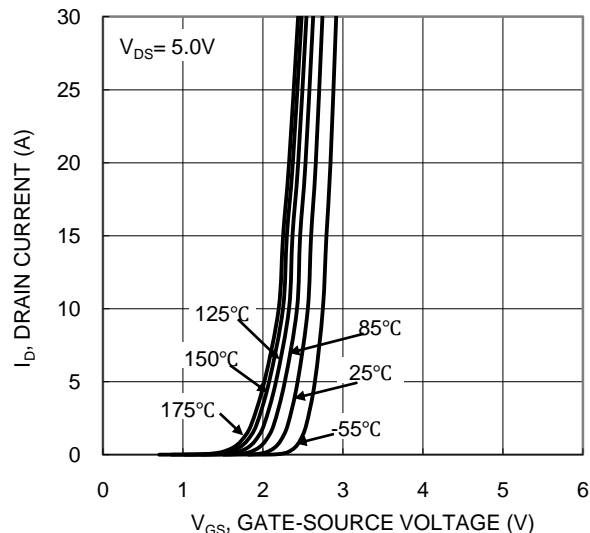


Figure 2. Typical Transfer Characteristic

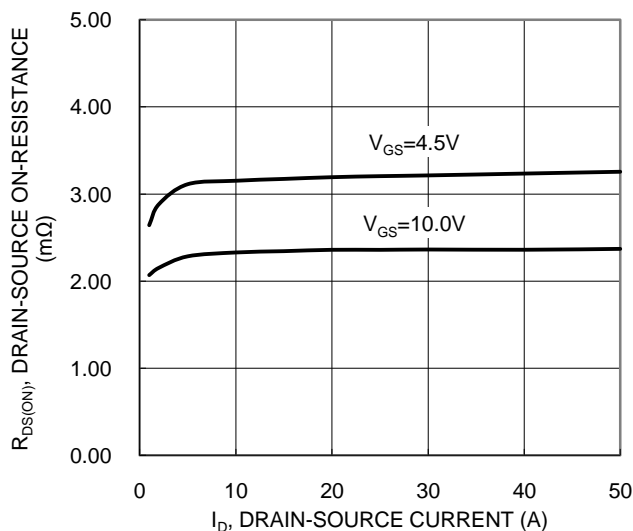


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

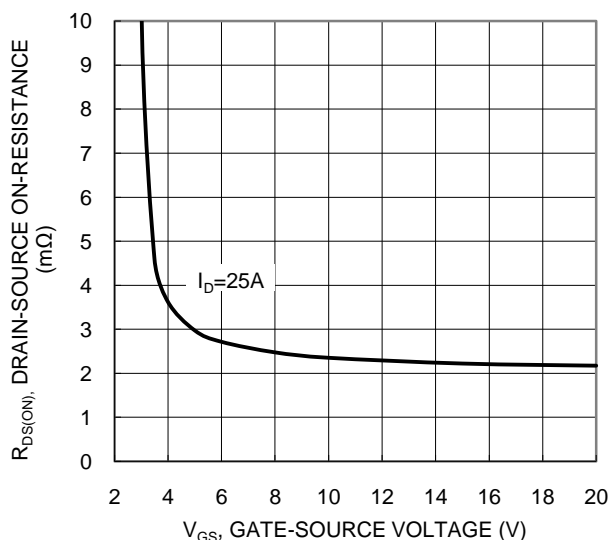


Figure 4. Typical Transfer Characteristic

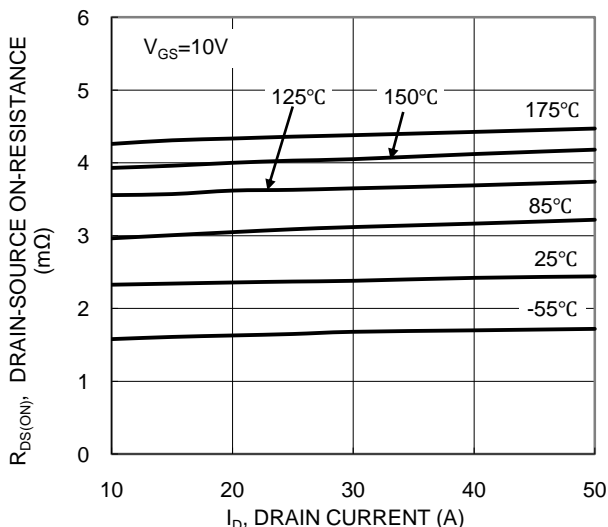


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

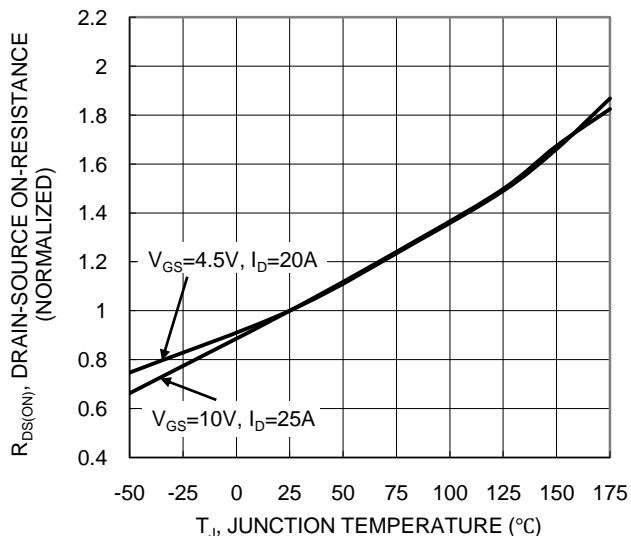


Figure 6. On-Resistance Variation with Temperature

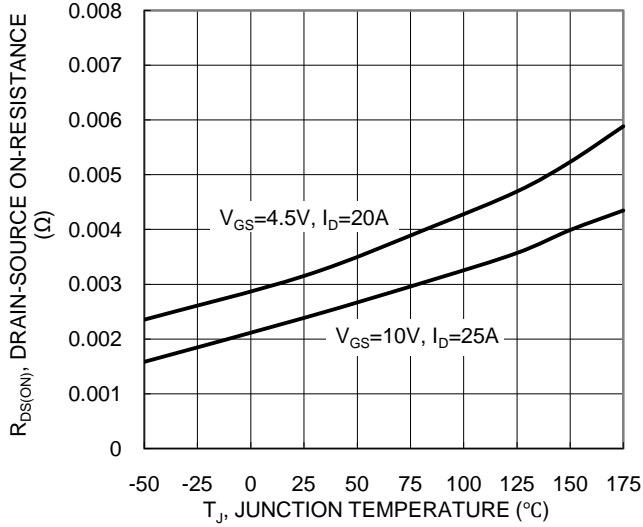


Figure 7. On-Resistance Variation with Temperature

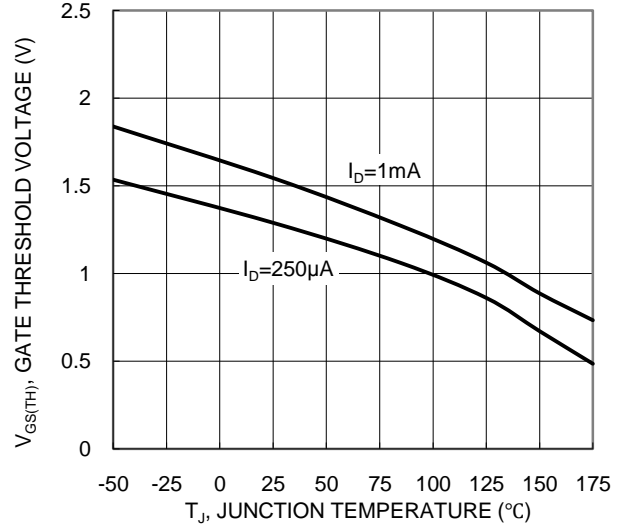


Figure 8. Gate Threshold Variation vs. Temperature

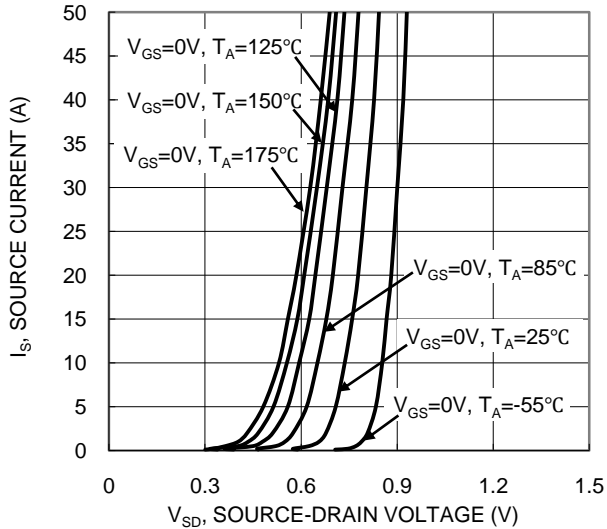


Figure 9. Diode Forward Voltage vs. Current

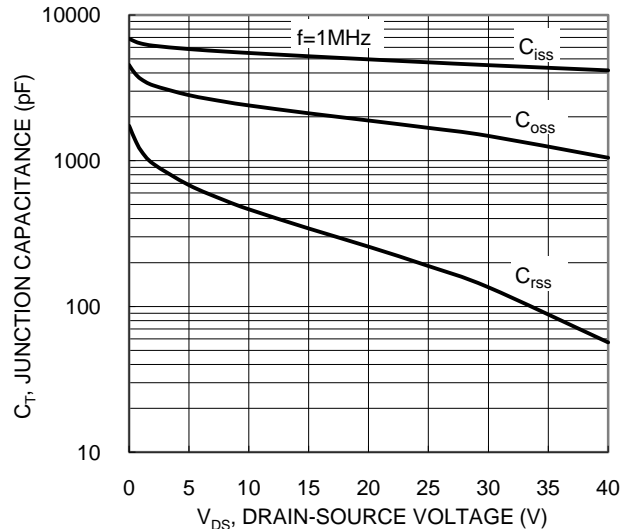


Figure 10. Typical Junction Capacitance

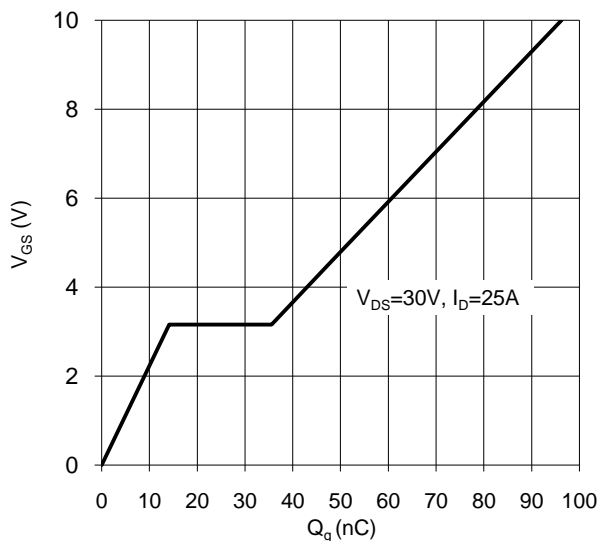


Figure 11. Gate Charge

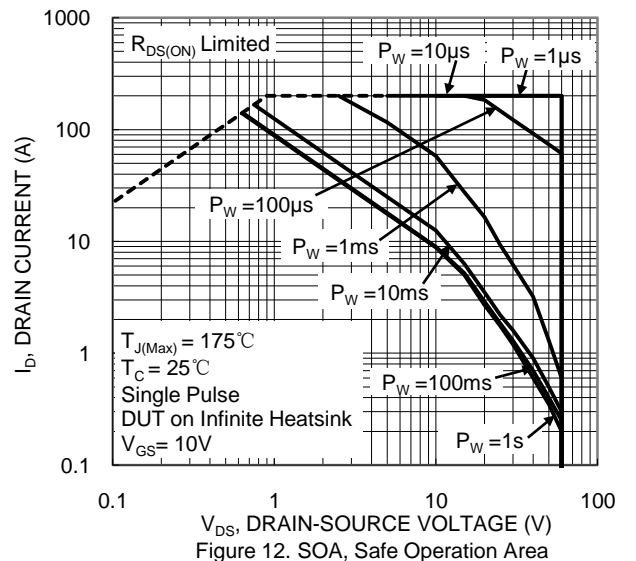


Figure 12. SOA, Safe Operation Area

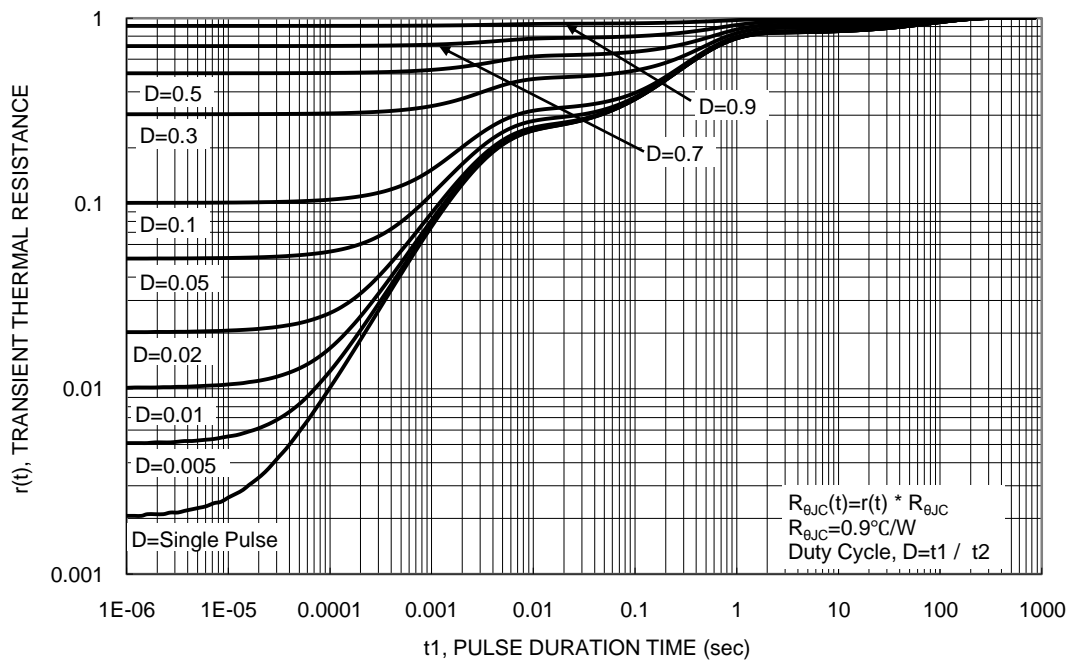
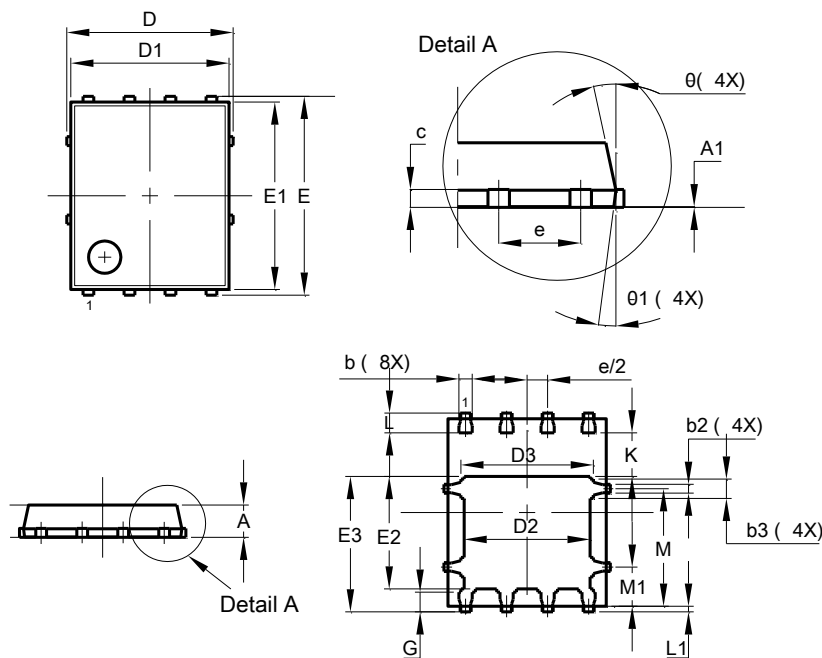


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

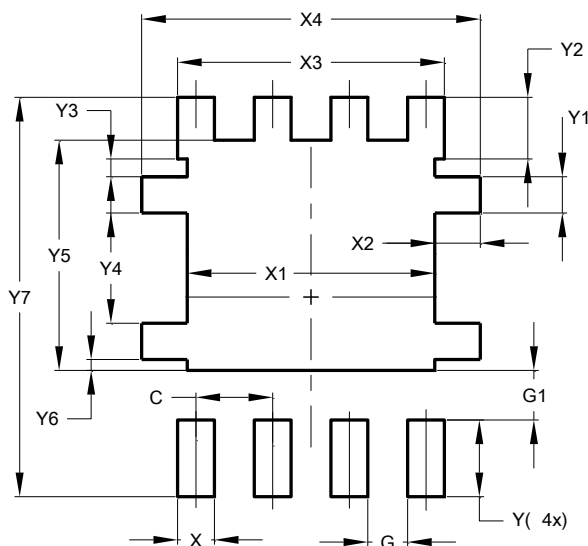
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



POWERDI [®] 5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	-
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	-	-
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
$\theta1$	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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